	Application No.	Applicant(s)	Applicant(s)	
Notice of Allowability	10/766,188	MINE ET AL.		
	Examiner	Art Unit		
	Ngan Ngo	2814		
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI	(OR REMAINS) CLOSED or other appropriate comn GHTS. This application is	in this application. If not include nunication will be mailed in due	ed course. <b>THIS</b>	
1. This communication is responsive to				
2. 🗵 The allowed claim(s) is/are <u>1-20</u> .				
3. $igotimes$ The drawings filed on <u>29 January 2004</u> are accepted by the	e Examiner.			
4.  Acknowledgment is made of a claim for foreign priority una a)  All b)  Some* c)  None of the:  1.  Certified copies of the priority documents have  2.  Certified copies of the priority documents have  3.  Copies of the certified copies of the priority documents have  International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.  5.  A SUBSTITUTE OATH OR DECLARATION must be submin INFORMAL PATENT APPLICATION (PTO-152) which give  6.  CORRECTED DRAWINGS (as "replacement sheets") must (a)  including changes required by the Notice of Draftspers  1)  hereto or 2)  To Paper No./Mail Date  Paper No./Mail Date  10  Paper No./Mail Date  11  Paper No./Mail Date  12  Paper No./Mail Date  13  Paper No./Mail Date  14  Paper No./Mail Date  15  Paper No./Mail Date  16  Paper No./Mail Date  17  Paper No./Mail Date  17  Paper No./Mail Date  17  Paper No./Mail Date  18  Paper No./Mail Date  18  Paper No./Mail Date  19  Paper	been received.  been received in Applicate cuments have been received of this communication to fill ENT of this application.  itted. Note the attached Exes reason(s) why the oath of the submitted.  son's Patent Drawing Reviews Amendment / Comment of the submitted of the submitt	ion No  ed in this national stage applicated in this national stage applicated in this national stage applicated in the red (AMINER'S AMENDMENT or Nor declaration is deficient.  ew ( PTO-948) attached or in the Office action of the drawings in the front (not the FR 1.121(d).	quirements	
<ul> <li>Attachment(s)</li> <li>1. ☑ Notice of References Cited (PTO-892)</li> <li>2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)</li> <li>3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 0104)</li> <li>4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material</li> </ul>	6. ☐ Interview : Paper No 98), 7. ☑ Examiner'	nformal Patent Application (PTo Summary (PTO-413), J./Mail Date s Amendment/Comment s Statement of Reasons for Allo Jures 7 and 8. Jugan Van Ng Primary Exami	owance	

Application/Control Number: 10/766,188

Art Unit: 2814

## Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

## In the drawings:

Figures 7 and 8 are labeled "PRIOR ART". See MPEP 608.02(g).

Any inquiry concerning this communication should be directed to Examiner Ngan Ngo at telephone number (571) 272-1711. The fax number for the Art unit is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

Ngan Van Ngo Primary Examiner

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Ngan Ngo

7/30/04

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## Reasons for Allowance

The following is an examiner's statement of reasons for allowance:

The prior arts of record do not teach the nonvolatile semiconductor memory device having "said charge trapping film comprises a silicon oxynitride film and a third insulator film in which the sum of the energy between a vacuum level and a conduction band of said third insulator film and a band gap of said third insulator film is smaller than that of said silicon oxynitride film; and wherein the product of a charge trap density and a film thickness of said silicon oxynitride film is larger than that of said third insulator film" in claim 1 and the "potential barrier film is 1 nm or less in thickness" in claim 18. The prior arts of record do not teach nonvolatile semiconductor memory device having only the potential barrier film and the silicon oxynitride film formed between the substrate and the gate electrode as claimed in claim 16

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

`Ngan Van Ngo >rimary Examiner